

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

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In re Patent Application of:  
Katsuki HAZAMA

Application No.: To be assigned  
(Div. of 09/438,295)

Filed: Concurrently Herewith

Art Unit: 2785

For: MULTILEVEL SEMICONDUCTOR  
MEMORY, WRITE/READ METHOD  
THERE TO/THEREFROM AND STORAGE  
MEDIUM STORING WRITE/READ  
PROGRAM

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Examiner: Not Yet Assigned

**FIRST PRELIMINARY AMENDMENT**

MS Non-Fee Amendment  
Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Dear Sir:

**INTRODUCTORY COMMENTS**

Prior to examination on the merits, please amend the above-identified U.S. patent application as follows:

**Amendments to the Specification** begin on page 2 of this paper.

**Amendments to the Claims** are reflected in the listing of claims which begins on page 4 of this paper.

**Remarks/Arguments** begin on page 5 of this paper.